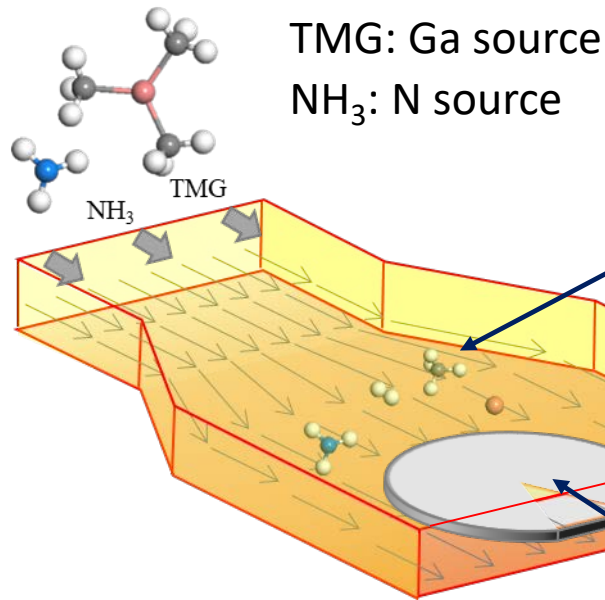
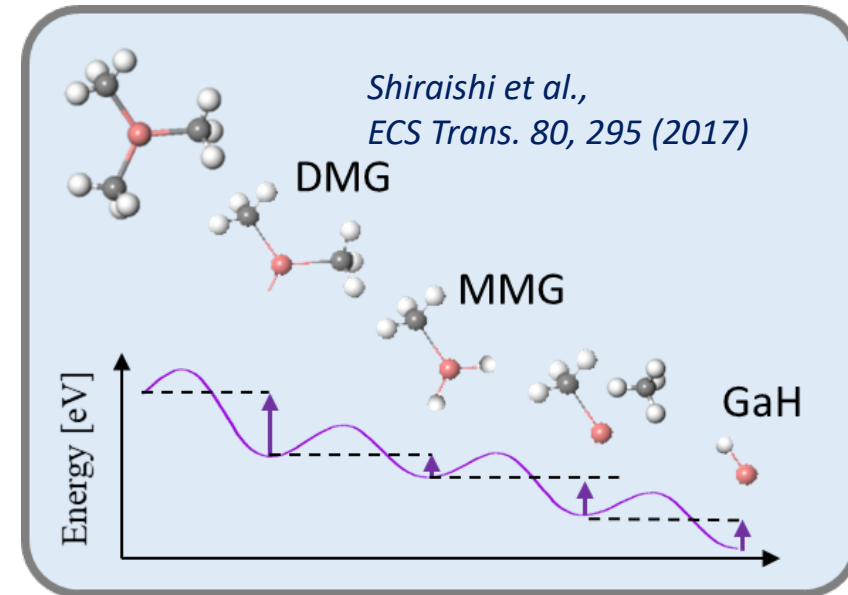


# MetalOrganic Vapor Phase Epitaxy (MOVPE) of GaN



TMG is decomposed in the gas phase



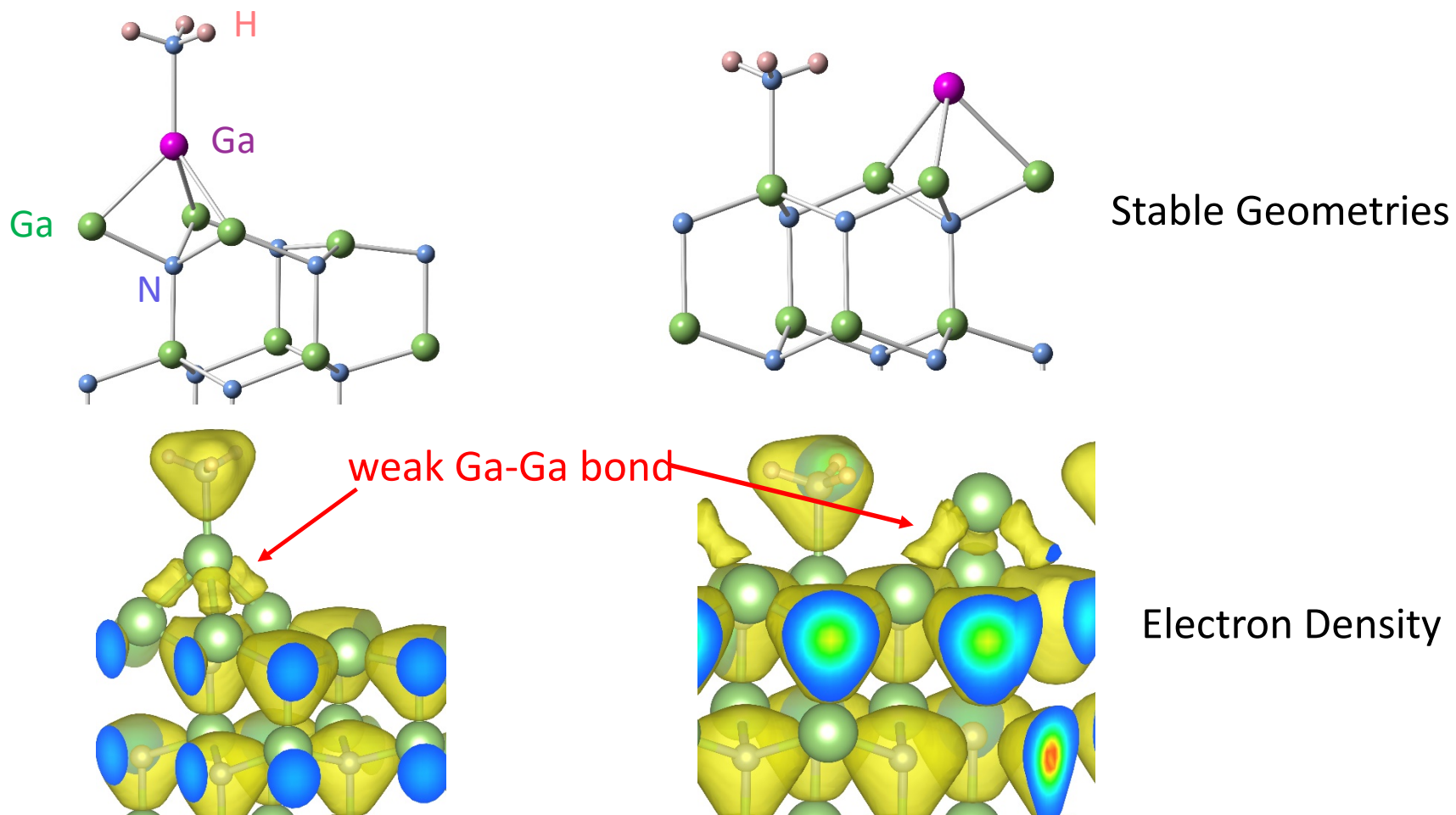
Decomposition of NH<sub>3</sub> is **UNKOWN**. But,,,**High-ResolutionTOF measurements** in Amano group show the existence of **only NH<sub>3</sub>** in the gas phase plus very **small amount (0.1 %)** of NH<sub>2</sub>.

Nagamatsu et al., Phys. Sttus Solidi B 254, 1600737 (2017)

**Need to know:**

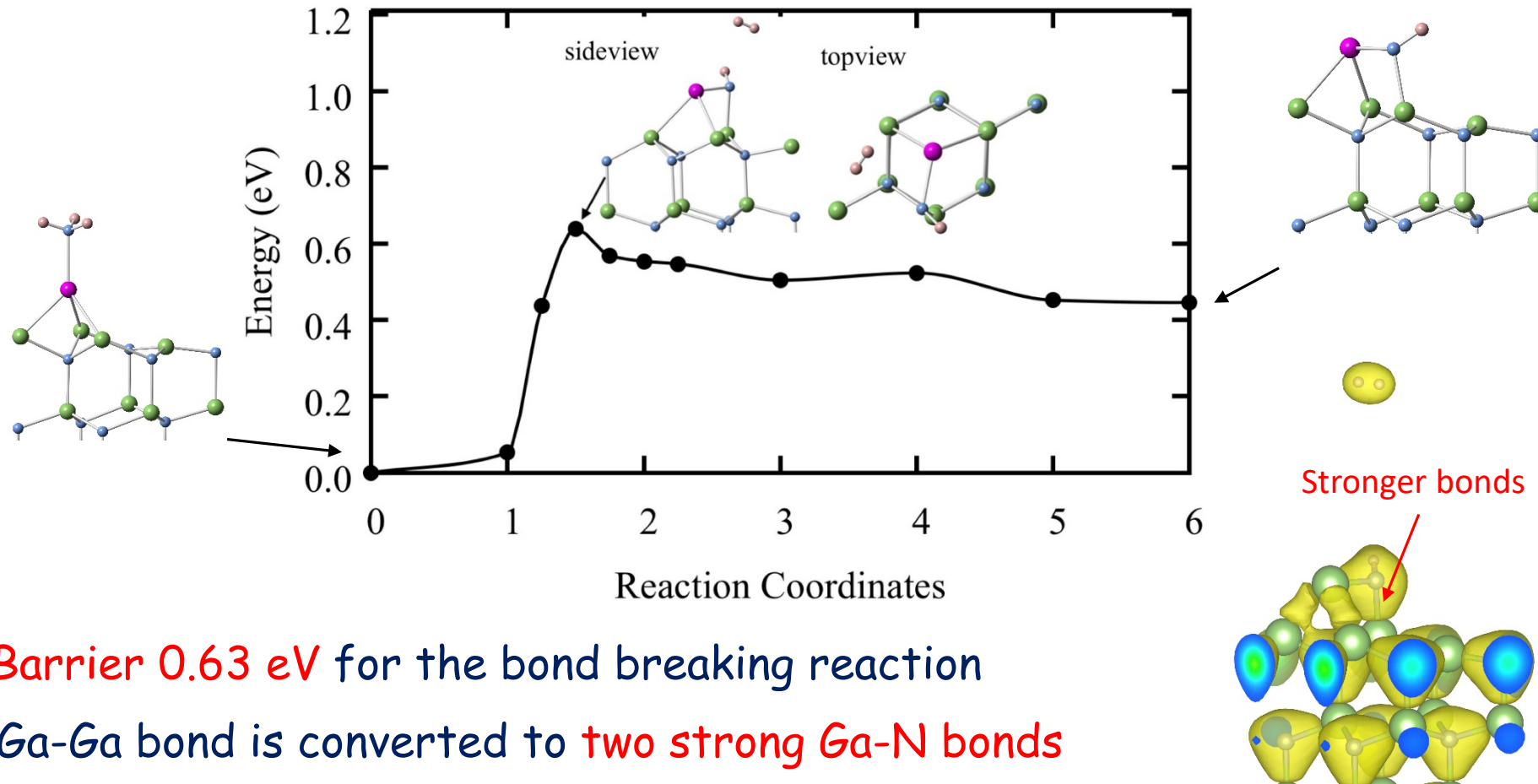
Behaviors of NH<sub>3</sub> and possible NH<sub>x</sub> on the growing surface, which is Ga rich

# NH<sub>3</sub> Adsorption on Ga-rich Surface



Ga dangling bond UNOCCUPIED: Electron Counting Rule

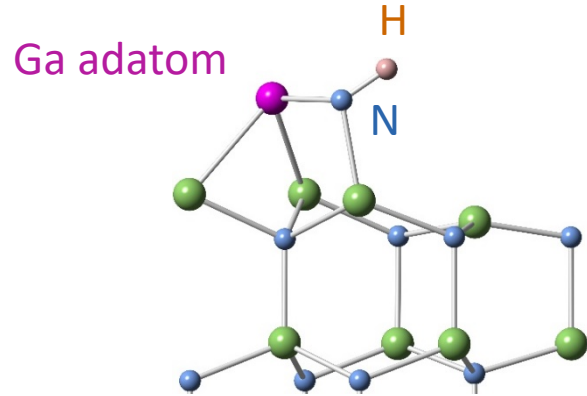
# Decomposition of $\text{NH}_3$ ( $\text{NH}_3 \rightarrow \text{NH}/\text{GaN} + \text{H}_2$ )



- ✓ Small Barrier 0.63 eV for the bond breaking reaction
- ✓ Weak Ga-Ga bond is converted to two strong Ga-N bonds
- ✓ When we consider free-energy gain of  $\text{H}_2$  in the gas phase,  
$$\mu_{\text{H}_2} = -k_B T \ln[g k_B T / p \zeta_{\text{trans}} \zeta_{\text{rot}} \zeta_{\text{vibr}}] = -2.1 \text{ eV}$$
 under growth condition  
the reaction becomes exothermic

# Diffusion of the NH unit on GaN(0001) Adatom Surface

## Stable NH Unit

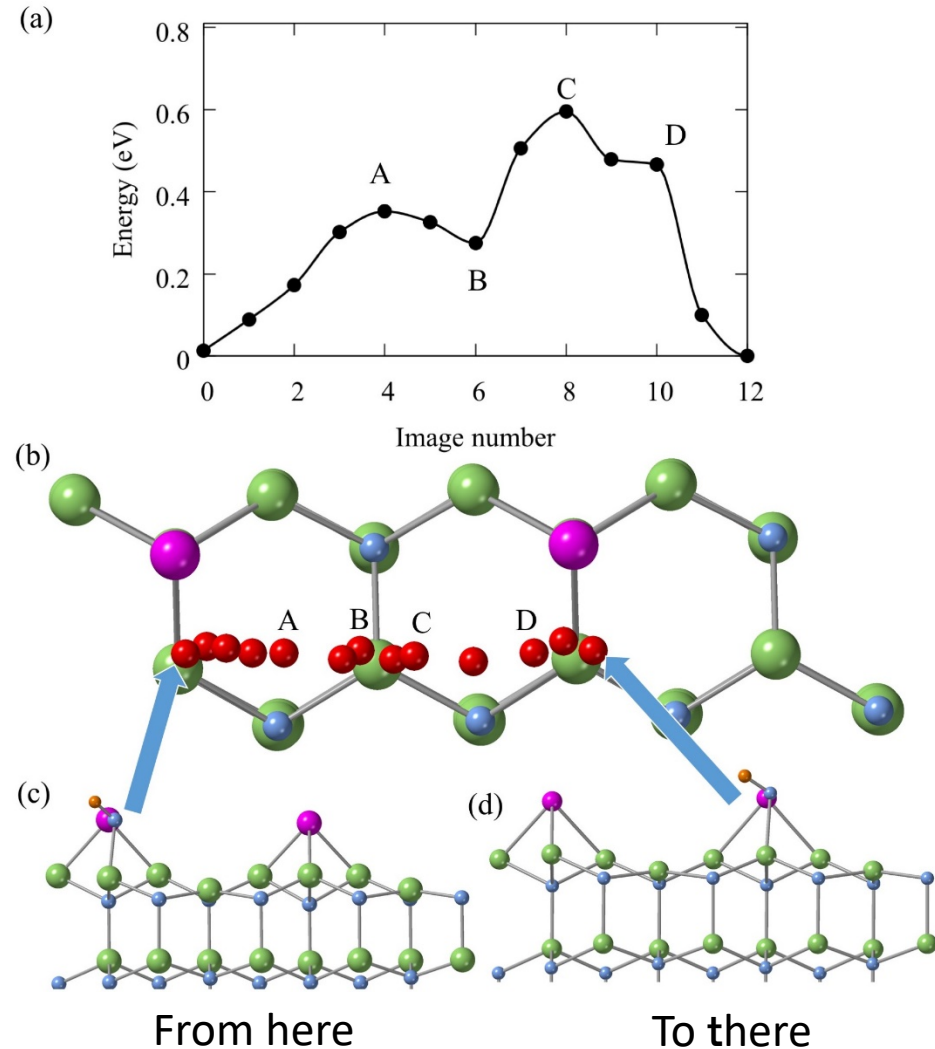


## Diffusion to the Adjacent Ga-adatom site

Search for the diffusion pathway by  
Hyperplane Constraint Method  
Diffusion barrier = 0.59 eV



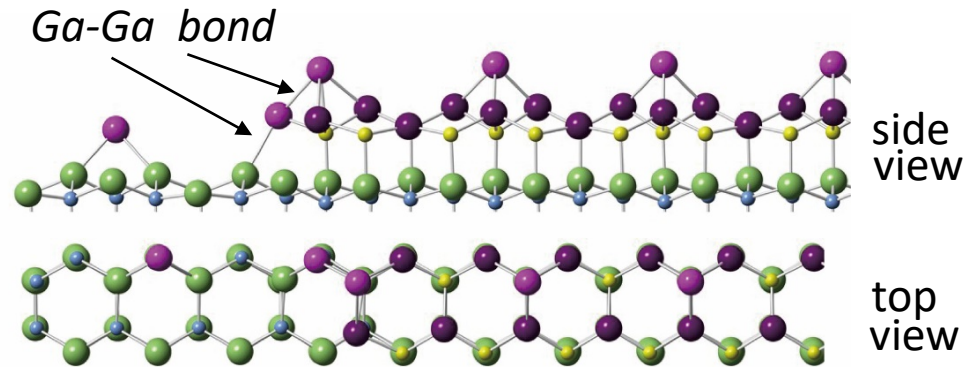
*NH unit wanders on the terrace and  
is expected to approach surface steps*



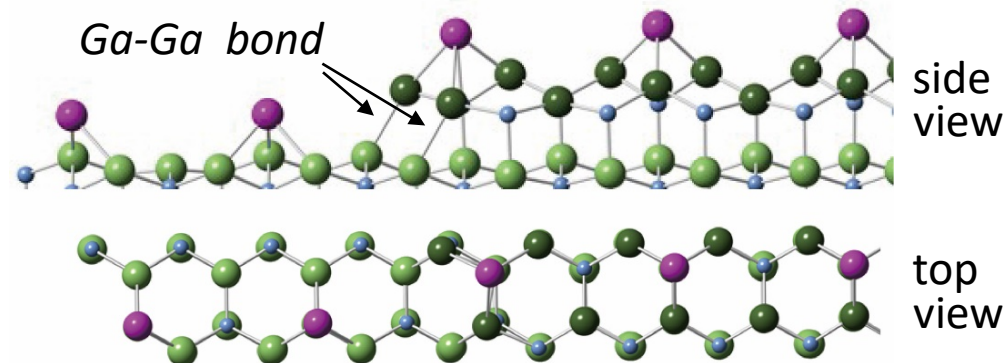
# Electron Density at Step Edges: Ga-Ga Weak Bonds

● ● ● [Ga Atoms near Step Edges]

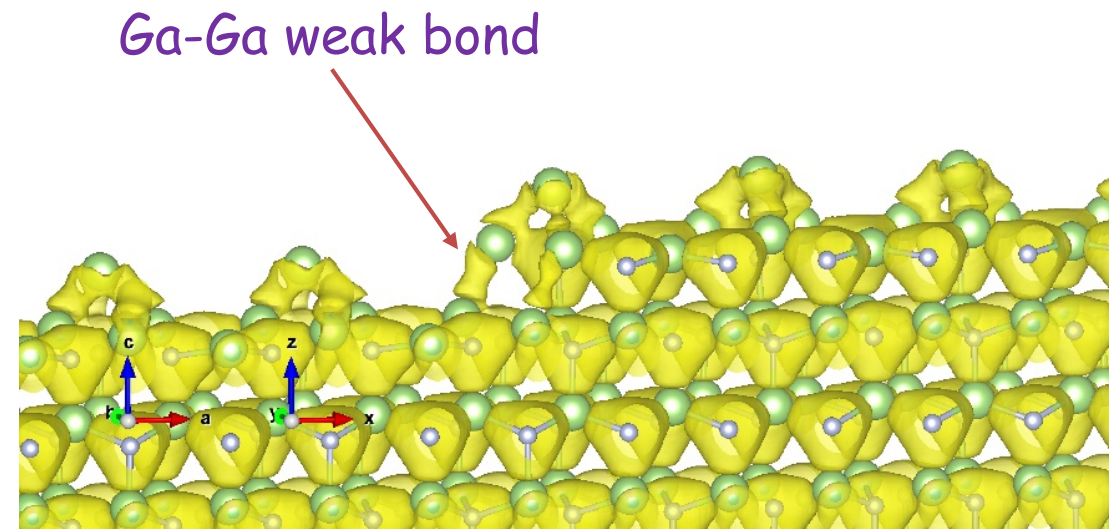
## GN Step



## Ga2 Step



## Electron Density near GN Step Edge

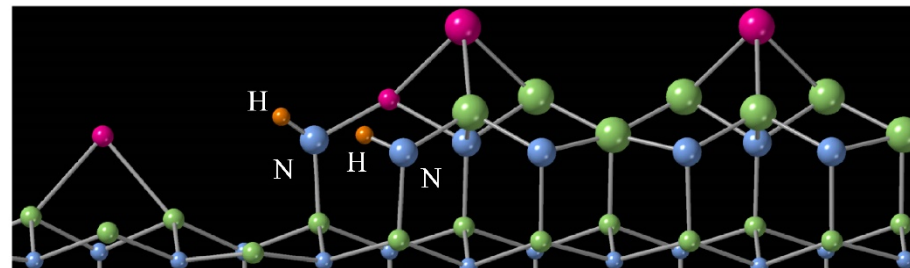
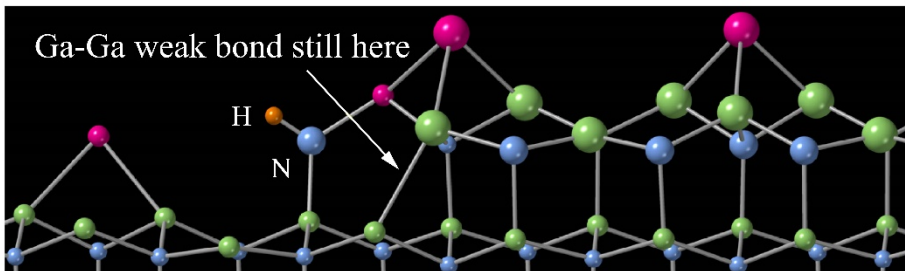


*Ga-Ga weak bond:  
Hot spot for the growth*



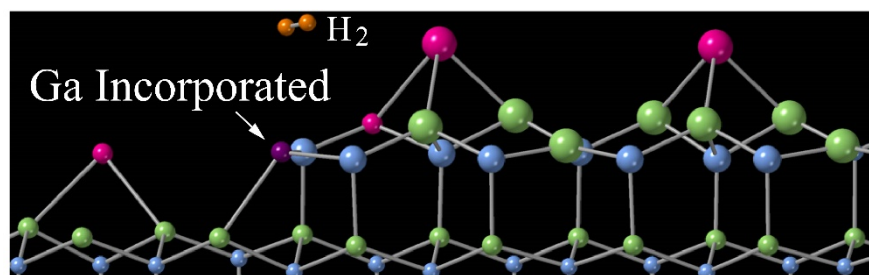
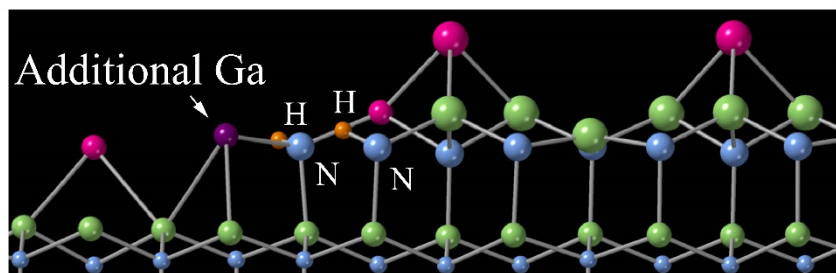
# NH Incorporation at GN Step Edges,,, and then Step-Flow Growth

## NH Intervening in Ga-Ga Weak Bonds at GN Step Edges

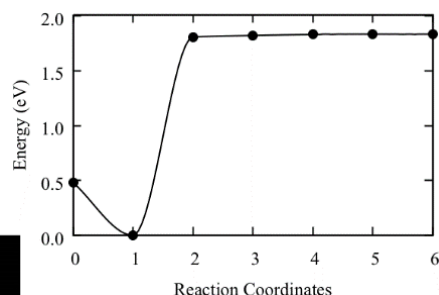


✓ 2 isolated NH in Ga-Ga bond on terrace  $\rightarrow$  2 NH at step edge + 0.45 eV Exothermic Attraction at Step Edges

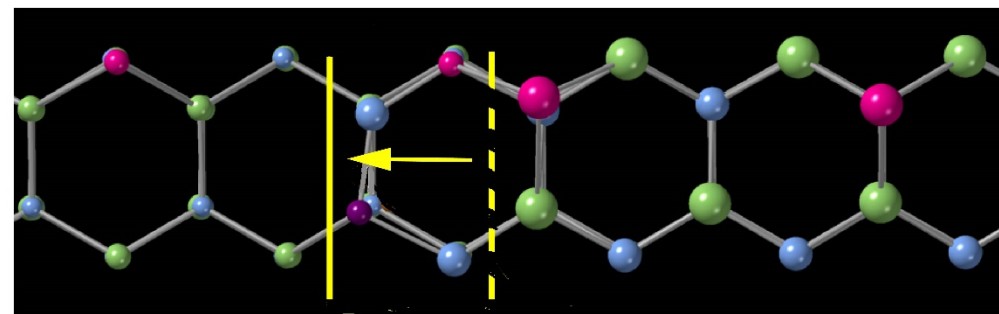
## New Ga on Ga-rich Surface $\rightarrow$ Incorporation of the new Ga with H<sub>2</sub> Desorbed



$\Delta F$  of H<sub>2</sub> = -2.1 eV



top view



Step Edge Proceeds

Possible Microscopic Process of Step-Flow Growth